

**2N6604**

**The RF Line**

**NPN SILICON HIGH FREQUENCY TRANSISTOR**

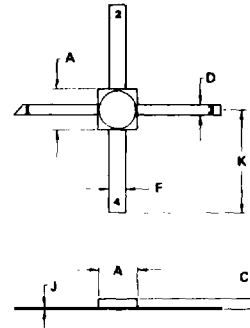
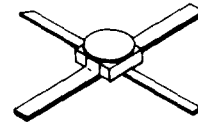
... designed for use in high-frequency, low-noise, small-signal, narrow and wideband amplifiers. Ideal for use in microstrip thin and thick film applications.

- Low Noise Figure – NF = 2.7 dB (Typ) @ f = 1.0 GHz
- High Power Gain –  $G_U(\text{max}) = 16 \text{ dB}$  (Typ) @ f = 1.0 GHz
- High Current – Specified Performance @  $I_C = 30 \text{ mA}$
- Ion Implantation and Gold Metallization
- Metal/Ceramic Hermetic Package
- JAN, JTXV Available

NF = 2.7 dB @ 1.0 GHz

**HIGH FREQUENCY  
 TRANSISTOR  
 NPN SILICON**

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STYLE 1  
 PIN 1 COLLECTOR  
 2 EMITTER  
 3 BASE  
 4 EMITTER

NOTE  
 1 DIMENSION "K" APPLIES TO ALL LEADS  
 2 DIRECTION OF 45° CUT ON PIN 1 IS VENDOR OPTION

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.29	2.67	0.090	0.105
B	0.89	1.40	0.035	0.055
C	0.41	0.51	0.016	0.024
D	0.89	1.09	0.035	0.043
F	0.98	0.15	0.063	0.006
K	4.45	5.84	0.175	0.230

**CASE 303-01**

**\*MAXIMUM RATINGS (T<sub>A</sub> = 25°C Free Air Temperature)**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	15	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	25	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	Vdc
Collector Current—Continuous	I <sub>C</sub>	50	mAdc
Total Device Dissipation @ T <sub>C</sub> = 125°C Derate Above 75°C	P <sub>D</sub>	500	mW
		6.66	mW/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C

\*Indicates JEDEC Registered Data.

**Specifications and Package Options**

Devices using the same die type as the 2N6604:

- MRF911 – 4 Lead Plastic Macro-T Case 302-01
- MRF914 – TO-72
- MMBR930 – MiniBloc Plastic (SOT-23) TO-236
- BFR91 – 3 Lead Plastic Macro-T Case 302A-01
- BFR91 – Unencapsulated Chip

# 2N6604

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

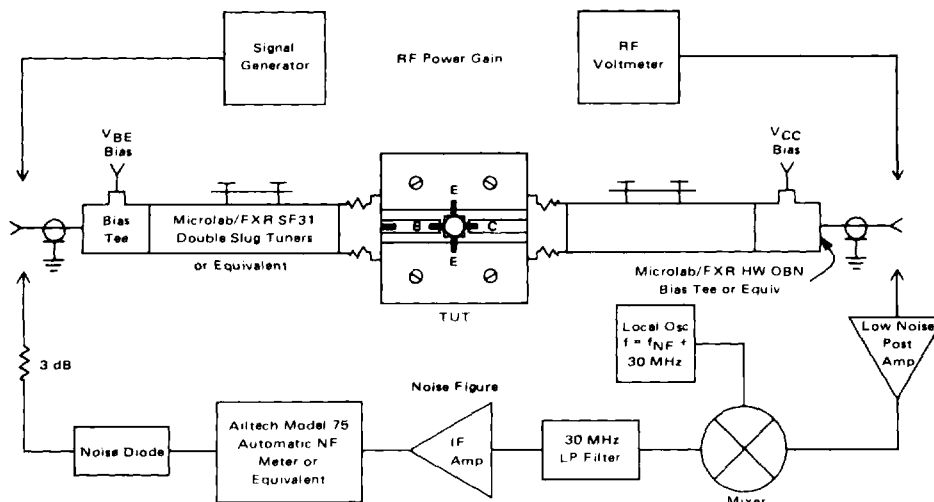
Characteristic	Symbol	Min	Typ	Max	Unit
<b>*OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 0.1 \text{ mAdc}, I_E = 0$ )	$V_{(BR)CBO}$	25	—	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 0.1 \text{ mAdc}, I_C = 0$ )	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ( $V_{CB} = 15 \text{ Vdc}, I_E = 0$ )	$I_{CBO}$	—	—	50	nAdc
<b>*ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 30 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ )	$h_{FE}$	30	—	200	—
<b>*DYNAMIC CHARACTERISTICS</b>					
Collector-Base Capacitance (1) ( $V_{CB} = 10 \text{ Vdc}, I_E = 0, 0.1 \text{ MHz} < f < 1.0 \text{ MHz}$ )	$C_{cb}$	0.30	—	0.80	pF
<b>*FUNCTIONAL TEST</b>					
Common-Emitter Amplifier Power Gain (Figure 2) ( $V_{CE} = 10 \text{ Vdc}, I_C = 30 \text{ mAdc}, f = 1.0 \text{ GHz}$ )	$G_{pe}$	15	—	21	dB
Spot Noise Figure ( $R_S = \text{Optimum} - \text{Figure 2}$ ) ( $V_{CE} = 10 \text{ Vdc}, I_C = 5.0 \text{ mAdc}, f = 1.0 \text{ GHz}$ )	NF	1.5	—	3.0	dB
Power Gain at Optimum Noise Figure ( $V_{CE} = 10 \text{ Vdc}, I_C = 5.0 \text{ mAdc}, f = 1.0 \text{ GHz}$ )	$G_{NF}$	9.0	—	—	dB
<b>TYPICAL 2 GHz PERFORMANCE</b>					
Maximum Unilateral Gain (Figure 2) (2) ( $V_{CE} = 10 \text{ Vdc}, I_C = 30 \text{ mAdc}, f = 2.0 \text{ GHz}$ )	$G_U(\text{max})$	—	10	—	dB
Noise Figure ( $R_S = \text{Optimum} - \text{Figure 2}$ ) ( $V_{CE} = 10 \text{ Vdc}, I_C = 5.0 \text{ mAdc}, f = 2.0 \text{ GHz}$ )	NF	—	4.3	—	dB

\*Indicates JEDEC Registered Data.

(1)  $C_{cb}$  measurement employs a three-terminal capacitance bridge incorporating a guard circuit. The emitter terminal shall be connected to the guard terminal of the bridge.

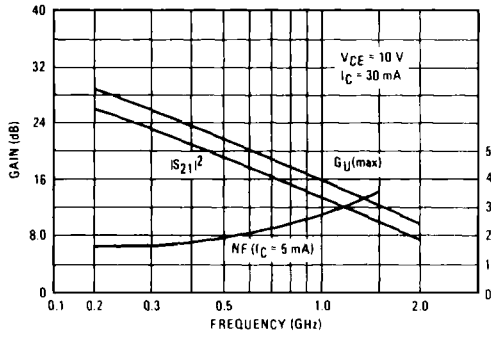
(2)  $G_U(\text{max})$  is calculated from the S Parameters using the equation  $G_U(\text{max}) = \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$

FIGURE 1 – BLOCK DIAGRAM FOR POWER GAIN AND NOISE FIGURE

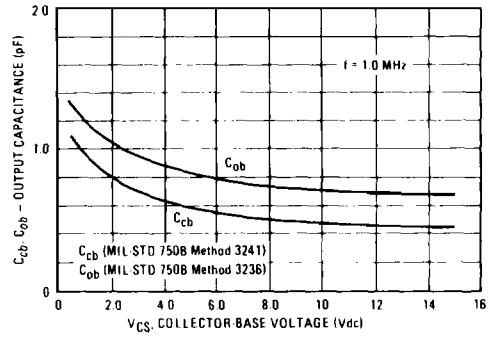


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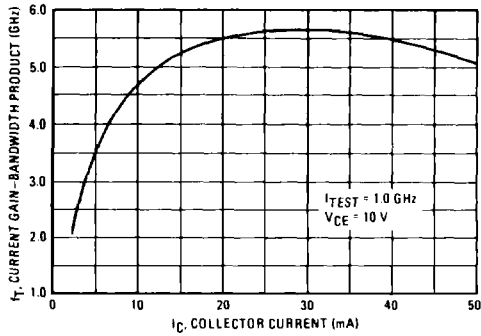
**FIGURE 2 – POWER GAIN AND NOISE FIGURE versus FREQUENCY**



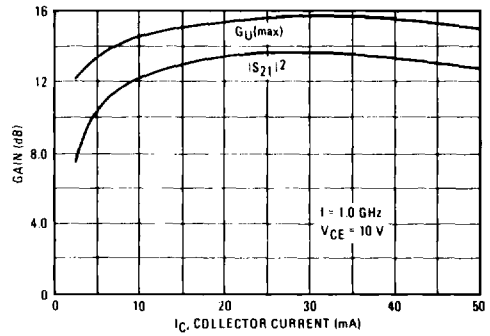
**FIGURE 3 – OUTPUT CAPACITANCE versus VOLTAGE**



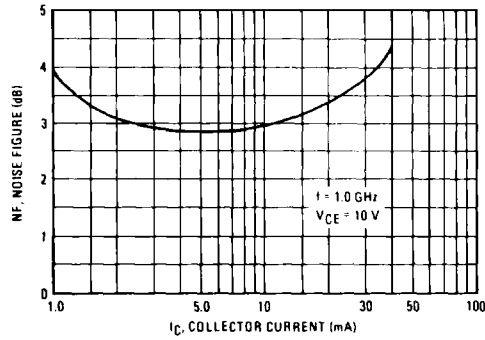
**FIGURE 4 – CURRENT GAIN-BANDWIDTH PRODUCT versus COLLECTOR CURRENT**



**FIGURE 5 – POWER GAIN versus COLLECTOR CURRENT**



**FIGURE 6 – NOISE FIGURE versus COLLECTOR CURRENT**



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## COMMON EMITTER SCATTERING PARAMETERS

FIGURE 7 - INPUT AND OUTPUT REFLECTION COEFFICIENTS versus FREQUENCY

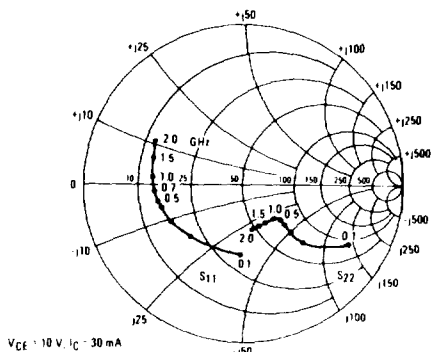
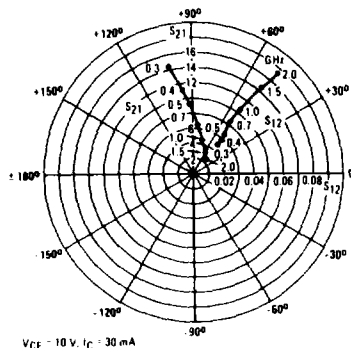


FIGURE 8 - FORWARD AND REVERSE TRANSMISSION COEFFICIENTS versus FREQUENCY



### S - PARAMETERS

VCE (Volts)	IC (mA)	Frequency (MHz)	S11		S21		S12		S22	
			S11	∠φ	S21	∠φ	S12	∠φ	S22	∠φ
5.0	5	100	0.72	-40	12.37	153	0.028	67	0.91	-18
		200	0.65	-78	10.38	133	0.048	51	0.76	-32
		500	0.61	-137	5.75	100	0.067	34	0.50	-45
		1000	0.61	-168	3.13	78	0.082	31	0.41	-54
		2000	0.63	161	1.58	47	0.112	30	0.41	-80
	10	100	0.57	-60	19.54	146	0.024	63	0.85	-27
		200	0.55	-105	14.70	125	0.038	47	0.64	-43
		500	0.59	-155	7.12	95	0.051	39	0.37	-55
		1000	0.61	-178	3.77	76	0.069	40	0.29	-62
		2000	0.64	156	1.91	50	0.106	39	0.30	-86
	30	100	0.43	-111	30.58	135	0.016	57	0.72	-39
		200	0.53	-145	19.35	114	0.022	49	0.46	-57
		500	0.62	-173	8.42	91	0.035	51	0.24	-69
		1000	0.63	172	4.36	75	0.058	54	0.18	-76
		2000	0.67	151	2.19	52	0.099	49	0.21	-99
	50	100	0.46	-134	32.34	129	0.013	57	0.64	-42
		200	0.57	-158	19.19	110	0.018	51	0.40	-56
		500	0.64	-178	8.13	89	0.031	57	0.22	-62
		1000	0.65	170	4.17	74	0.053	58	0.19	-70
		2000	0.70	150	2.10	52	0.092	54	0.22	-97
10	5	100	0.74	-36	12.34	154	0.023	69	0.93	-15
		200	0.67	-71	10.56	135	0.040	54	0.81	-25
		500	0.59	-131	6.09	102	0.058	37	0.57	-36
		1000	0.58	-164	3.32	79	0.073	33	0.50	-44
		2000	0.60	164	1.67	48	0.098	32	0.49	-69
	10	100	0.60	-52	19.75	148	0.020	65	0.87	-21
		200	0.56	-95	15.30	127	0.032	49	0.69	-33
		500	0.56	-149	7.69	97	0.044	41	0.45	-41
		1000	0.58	-174	4.07	77	0.061	42	0.39	-47
		2000	0.61	159	2.03	50	0.095	40	0.39	-70
	30	100	0.44	-94	32.03	136	0.014	59	0.75	-31
		200	0.50	-135	20.76	115	0.021	49	0.52	-41
		500	0.57	-168	9.13	91	0.032	52	0.33	-43
		1000	0.59	175	4.71	75	0.052	54	0.29	-48
		2000	0.64	154	2.34	52	0.089	49	0.30	-72
	50	100	0.44	-117	33.56	129	0.012	59	0.68	-31
		200	0.52	-150	19.94	109	0.017	50	0.47	-36
		500	0.59	-174	8.52	89	0.028	56	0.34	-35
		1000	0.61	173	4.38	75	0.049	57	0.32	-43
		2000	0.66	152	2.21	51	0.083	52	0.34	-70